IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	Asok K Sarkar
Serial No.:	10/602,315	Group Art Unit:	2829
Filed:	June 24, 2003	Docket:	1303.107US1
Title:	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS		

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of $180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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Date 12 November 2004 By David R. Cochran
David R. Cochran
Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 12 day of November, 2004.

Name KACIA LEE

Signature Kacia Lee

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known	
Application Number	10/602,315
Filing Date	June 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2829
Examiner Name	Sarkar, Asok

Attorney Docket No: 1303.107US1

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EXAMINER **DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known

Application Number	10/602,315
Filing Date	June 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2829
Examiner Name	Sarkar, Asok

Sheet 2 of 4

Attorney Docket No: 1303.107US1

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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EXAMINER **DATE CONSIDERED**

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Substitute for form 1449A/PTO **INFORMATION DISCLOSURE STATEMENT BY APPLICANT** *(Use as many sheets as necessary)*	*Complete if Known*	
	Application Number	10/602,315
	Filing Date	June 24, 2003
	First Named Inventor	Ahn, Kie
	Group Art Unit	2829
	Examiner Name	Sarkar, Asok
Sheet 3 of 4	Attorney Docket No: 1303.107US1	

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	First Named Inventor	Ahn, Kie
	Group Art Unit	2829
	Examiner Name	Sarkar, Asok
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Serial No.:	10/602,315	Group Art Unit:	2829
Filed:	June 24, 2003	Docket:	1303.107US1
Title:	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS		

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

Serial/Patent No.	Filing Date	Attorney Docket	Title
09/944981	August 30, 2001	1303.021US1	GATE OXIDES AND METHODS OF FORMING
09/945535	August 30, 2001	1303.026US1	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2
10/052983 6767795	January 17, 2002	1303.031US1	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
10/027315	December 20, 2001	1303.033US1	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/081439	February 20, 2002	1303.046US1	EVAPORATED LaAIO3 FILMS FOR GATE DIELECTRICS
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10/163481	June 5, 2002	1303.056US1	ATOMIC LAYER-DEPOSITED HfAlO3 FILMS FOR GATE DIELECTRICS

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10/219870	August 15, 2002	1303.069US1	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION
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10/602323	June 24, 2003	1303.101US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
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10/765619	January 27, 2004	1303.033US2	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/768597	January 30, 2004	1303.033US3	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/789042	February 27, 2004	1303.050US2	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELECTRICS
10/789044	February 27, 2004	1303.070US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS
10/863953	June 9, 2004	1303.031US2	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
10/930138	August 31, 2004	1303.044US2	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELETRICS
10/930184	August 31, 2004	1303.021US2	CRYSTALLINE OR AMORPHOUS MEDIUM-K GATE OXIDES, Y2O3 AND GD203
10/930516	August 31, 2004	1303.078US2	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/931341	August 31, 2004	1303.082US2	ATOMIC LAYER DEPOSITED ZR-SN-TI-O FILMS USING TiI4
10/930431	August 31, 2004	1303.056US2	ATOMIC LAYER-DEPOSITED HfAlO3 FILMS FOR GATE DIELECTRICS
10/931365	August 31, 2004	1303.059US2	Pr2O3-BASED La-oxide GATE DIELECTRICS

10/931364	August 31, 2004	1303.069US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION
10/931343	August 31, 2004	1303.101US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/931340	August 31, 2004	1303.107US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
10/931356	August 31, 2004	1303.026US2	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2

Respectfully submitted,

KIE Y. AHN ET AL.

By Applicants' Representatives,

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Minneapolis, MN 55402
(612) 371-2157

Date 12 November 2004 By _____
David R. Coehran
Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 12 day of November, 2004.

KACIA LEE
Name

Kacia Lee
Signature